

EMH4FHA / UMH4NFHA / IMH4AFRA

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Datasheet

AEC-Q101 Qualified

Parameter	Tr1 and Tr2
V_{CEO}	50V
I _{C(MAX.)}	100mA
R ₁	10kΩ

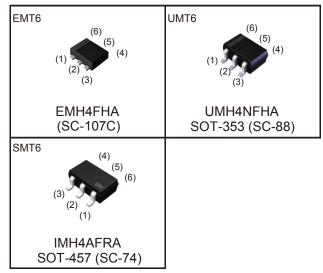
Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC114T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

Application

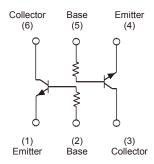
Inverter circuit, Interface circuit, Driver circuit

Outline

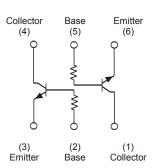


•Inner circuit

EMH4FHA / UMH4NFHA



IMH4AFRA



Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH4FHA	EMT6	1616	T2R	180	8	8,000	H4
UMH4NFHA	UMT6	2021	TR	180	8	3,000	H4
IMH4AFRA	SMT6	2928	T108	180	8	3,000	H4

● Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Paramete	er	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	50	V	
Collector-emitter voltage	V_{CEO}	50	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current		I _{C(MAX.)} *1	100	mA
Collector Power dissipation EMH4FHA / UMH4NFHA		P _D *2	150 (Total) ^{*3}	mW
IMH4AFRA		P_{D}	300 (Total) ^{*4}	mW
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	−55 to +150	°C

●Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μΑ
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 10mA / 1mA	-	-	0.3	V
DC current gain	h _{FE}	V_{CE} = 5V , I_{C} = 1mA ,	100	250	600	-
Input resistance	R ₁	-	7	10	13	kΩ
Transition frequency	f _T *1	$V_{CE} = 10V, I_{E} = -5mA,$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

^{*4 200}mW per element must not be exceeded.

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Grounded emitter propagation characteristics

10

(Yebelle SV)

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(Yebelle SV)

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(Yebelle SV)

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(Yebelle SV)

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(Yebelle SV)

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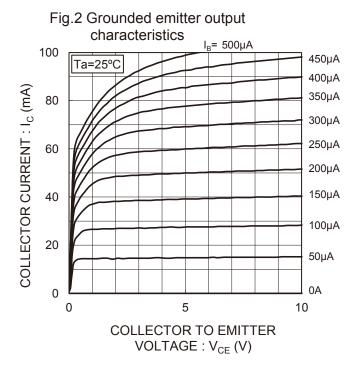
(Yebelle SV)

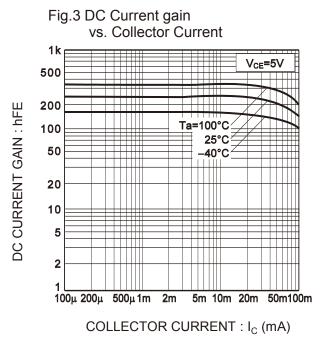
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(Yebelle SV)

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(Yebelle S





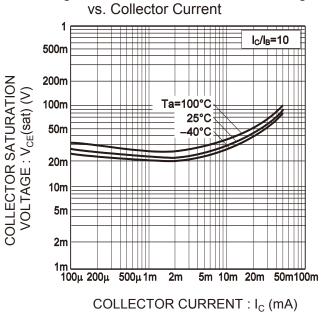
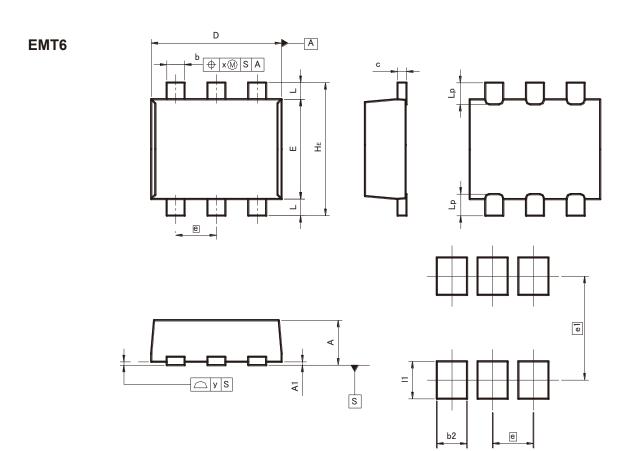


Fig.4 Collector-emitter saturation voltage

●Dimensions (Unit : mm)



Patterm of terminal position areas

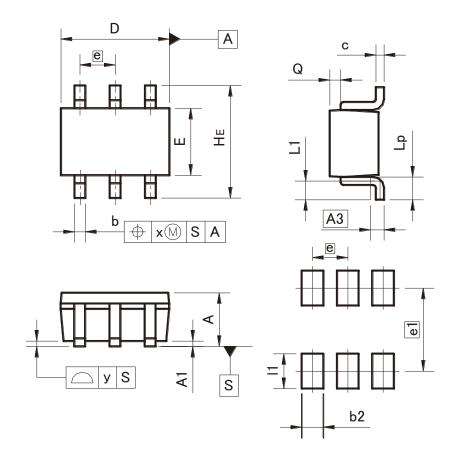
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
Α	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
С	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
Е	1.10	1.30	0.043	0.051	
е	0.9	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35	_	0.014	
х	_	0.10		0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
MIN		MAX	MIN	MAX	
e1	1.25		0.049		
b2	- 0.37		ı	0.015	
11	_	0.45	_	0.018	

Dimension in mm/inches

●Dimensions (Unit : mm)

UMT6



Patterm of terminal position areas

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	-	0.039	
A1	0.00	0.10	0	0.004	
A3	0.3	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
Х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

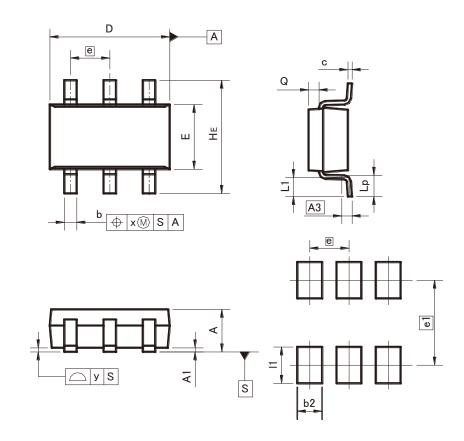
DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
e1	1.	1.55		06
b2	_	- 0.40		0.016
11	_	- 0.65		0.026

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Dimension in mm/inches

●Dimensions (Unit : mm)

SMT6



Patterm of terminal position areas

DIM	MILIM	MILIMETERS		HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.5	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM MIN		MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	_	0.024	
l1	_	0.90	_	0.035	

Dimension in mm/inches

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